

8kV 300mA HIGH VOLTAGE DIODE

ESJC30-08 is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Features

- High speed switching
- Low VF
- High surge resistivity for CRT discharge
- High reliability design
- Ultra small package

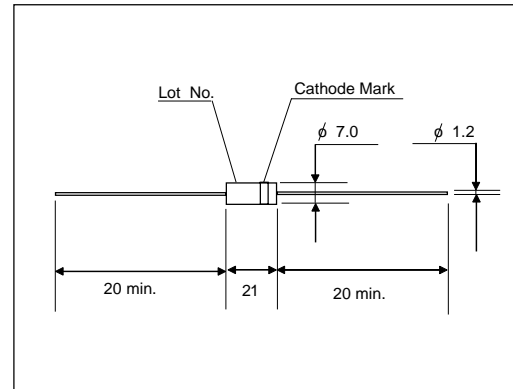
Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Outline Drawings : mm



Cathode Mark

| Type | Mark |
|-----------|------|
| ESJC30-08 | |

| Items | Symbols | Condition | ESJC30-08 | Units |
|--------------------------------------|-----------|---|-------------|--------------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 8.0 | kV |
| Average Output Current | I_o | $T_a=25^{\circ}\text{C}$, Resistive Load | 300 | mA |
| Surge Current | I_{FSM} | | 15 | A_{peak} |
| Junction Temperature | T_j | | 120 | $^{\circ}\text{C}$ |
| Allowable Operation Case Temperature | T_c | | 120 | $^{\circ}\text{C}$ |
| Storage Temperature | T_{stg} | | -40 to +125 | $^{\circ}\text{C}$ |

- Electrical Characteristics ($T_a=25^{\circ}\text{C}$ Unless otherwise specified)

| Items | Symbols | Conditions | ESJC30-08 | Units |
|-------------------------------|----------|---|-----------|---------------|
| Maximum Forward Voltage Drop | V_F | at 25°C , $I_F=I_{F(AV)}$ | 20 | V |
| Maximum Reverse Current | I_{R1} | at 25°C , $V_R=V_{RRM}$ | 5.0 | μA |
| | I_{R2} | at 100°C , $V_R=V_{RRM}$ | 50 | μA |
| Maximum Reverse Recovery Time | T_{rr} | at 25°C | 150 | nS |
| Junction Capacitance | C_j | at 25°C , $V_R=0\text{V}$, $f=1\text{MHz}$ | 15 | pF |